

THYRISTOR MODULE

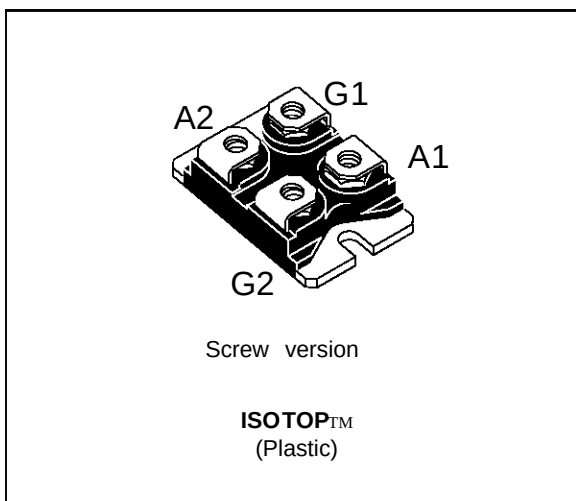
FEATURES

- $V_{DRM} = V_{RRM}$ UP TO 1400 V
- $I_T(RMS) = 70$ A
- HIGH SURGE CAPABILITY
- INSULATED PACKAGE :
INSULATING VOLTAGE 2500 V_(RMS)

DESCRIPTION

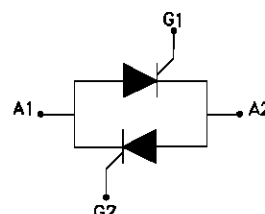
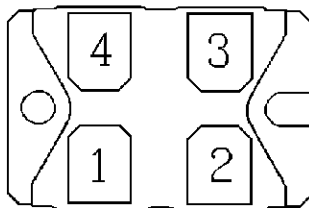
The MSS50 family are constituted of two general purpose SCR. Suitable for AC switching and phase control on resistive and inductive load up to 400 Hz.

The small volume (7cm³) and weight (29g) of the isotop package are well adapted to new generation of medium size module market applications.



PIN CONNECTIONS

- 1 : Thyristor 2 Anode (A2)
2 : Thyristor 2 Gate (G2)
3 : Thyristor 1 Anode (A1)
4 : Thyristor 1 Gate (G1)



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_T(RMS)$	RMS on-state current	$T_c = 80^\circ C$	70	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3ms$	630	A
		$t_p = 10ms$	600	
I_{2t}	I_{2t} value for fusing	$t_p = 10ms$	1800	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : $I_G = 800mA$ – $di_G/dt = 1A/\mu s$		100	A/ μs
T_{stg} T_j	Storage temperature range Operating junction temperature range		- 40 + 150 - 40 + 125	$^\circ C$

Symbol	Parameter	MSS50			Unit
		-800	-1200	-1400	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$	800	1200	1400	V

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	DC	0.75	°C/W
		AC	0.45	
Rth (j-h)	Contact (case to heatsink) (4)		0.05	°C/W

(4) With contact grease utilisation

GATE CHARACTERISTICS (maximum values)

 $P_{GM} = 50 \text{ W}$ ($t_p = 20 \mu\text{s}$) $P_G (AV) = 1 \text{ W}$ $I_{FGM} = 4 \text{ A}$ ($t_p = 20 \mu\text{s}$) $V_{RGM} = 5 \text{ V}$.

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
I_{GT}	$V_D = 12 \text{ V}$ (DC) $R_L = 33 \Omega$	$T_j = 25^\circ\text{C}$	MAX	50	mA
V_{GT}	$V_D = 12 \text{ V}$ (DC) $R_L = 33 \Omega$	$T_j = 25^\circ\text{C}$	MAX	1.5	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$	$T_j = 125^\circ\text{C}$	MIN	0.2	V
tgt	$V_D = V_{DRM}$ $I_G = 500 \text{ mA}$ $di_G/dt = 3 \text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	TYP	2	μs
I_L	$I_G = 1.2 I_{GT}$	$T_j = 25^\circ\text{C}$	TYP	60	mA
			MAX	120	
I_H	$I_T = 0.5 \text{ A}$ gate open	$T_j = 25^\circ\text{C}$	TYP	40	mA
			MAX	80	
V_{TM}	$I_{TM} = 100 \text{ A}$ $t_p = 380 \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX	1.7	V
I_{DRM} I_{RRM}	V_{DRM} Rated V_{RRM} Rated	$T_j = 25^\circ\text{C}$	MAX	0.05	mA
		$T_j = 125^\circ\text{C}$	MAX	10	
tq	$I_T = 100 \text{ A}$ $V_R = 75 \text{ V}$ $V_D = 67\% V_{DRM}$ $di/dt = 30 \text{ A}/\mu\text{s}$ $dV/dt = 20 \text{ V}/\mu\text{s}$ Gate open	$T_j = 125^\circ\text{C}$	TYP	100	μs
dV/dt *	Linear slope up to $V_D = 67\% V_{DRM}$ gate open	$T_j = 125^\circ\text{C}$	MIN	500	V/ μs

* For higher guaranteed values, please consult us.

Note : MSS50-1400

- I_{DRM} and I_{RRM} at $T_j = 125^\circ\text{C}$ is defined at 1200 V
- dV/dt at $T_j = 125^\circ\text{C}$ is defined at 67% of 1200 V

Fig. 1 : Maximum RMS power dissipation versus RMS on-state current.
($F = 50$ Hz)

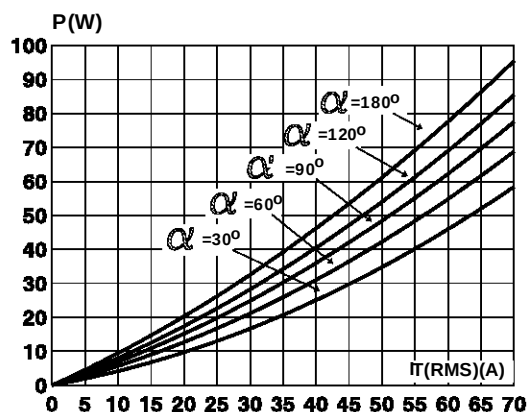


Fig. 2 : Correlation between maximum RMS power dissipation and maximum allowable temperature (T_{amb}) for different thermal resistances heatsink + contact.

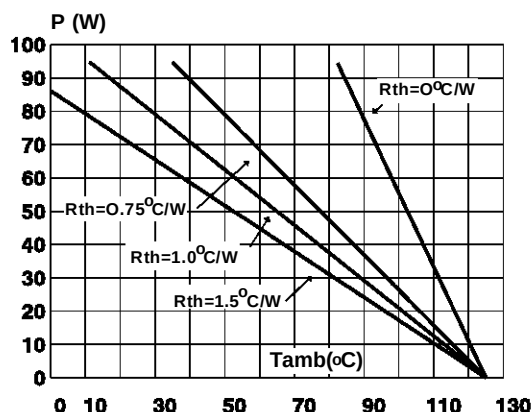


Fig. 3 : RMS on-state current versus case temperature.

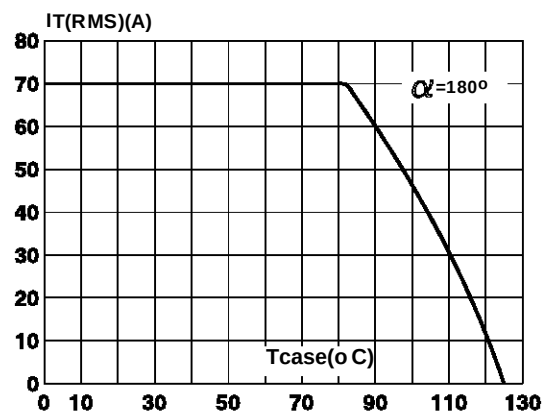


Fig. 4 : Thermal transient impedance junction to case versus pulse duration.

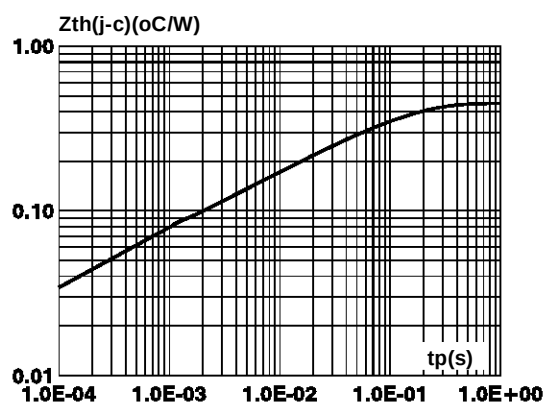


Fig. 5 : Relative variation of gate trigger and holding current versus junction temperature.

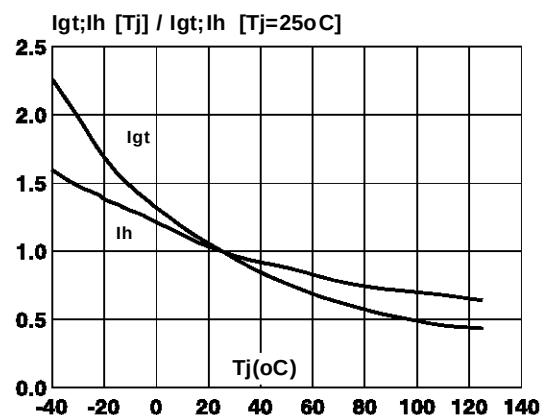


Fig. 6 : Non repetitive surge peak on-state current versus number of cycles.

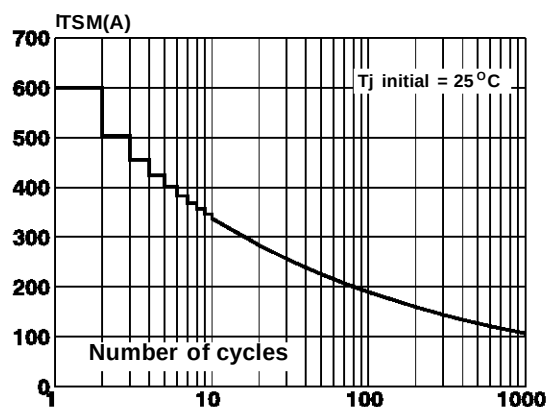


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10$ ms and corresponding value of I^2t .

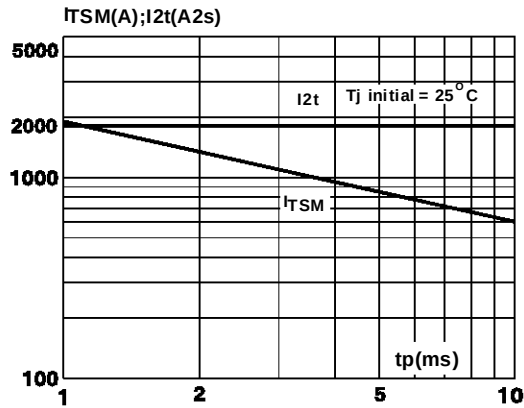
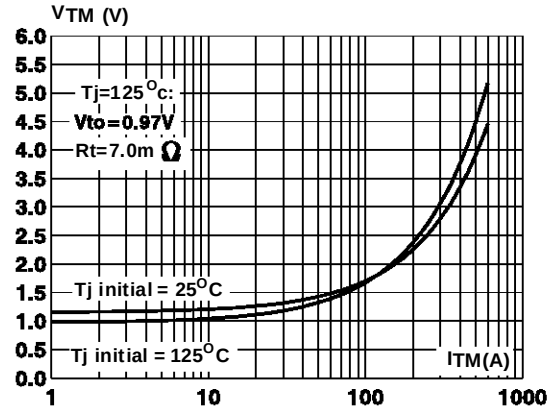
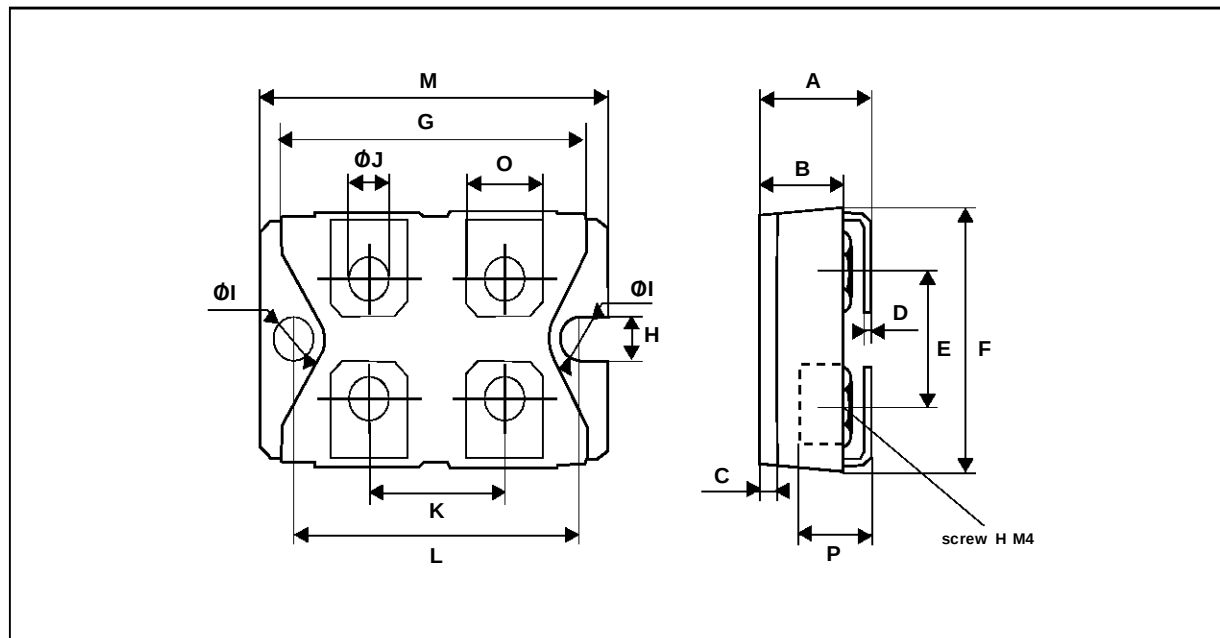


Fig. 8 : On-state characteristics .
(Maximum values)



PACKAGE MECHANICAL DATA

ISOTOP plastic : SCREW VERSION



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
B	8.90	9.10	0.350	0.358
C	1.95	2.05	0.077	0.081
D	0.75	0.85	0.029	0.034
E	12.60	12.80	0.496	0.504
F	25.10	25.50	0.988	1.004
G	31.50	31.70	1.240	1.248
H	4.00		0.157	
I	4.10	4.30	0.161	0.169
J	4.10	4.30	0.161	0.169
K	14.90	15.10	0.586	0.595
L	30.10	30.30	1.185	1.193
M	37.80	38.20	1.488	1.504
O	7.80	8.20	0.307	0.323
P	5.50		0.216	

Cooling method : C
 Marking : Type number
 Weight : 28 g. (without screws)
 Electrical isolation : 2500V(RMS)
 Capacitance : < 45 pF
 Inductance : < 5 nH

- Recommended torque value : 1.3 N.m (Max 1.5 N.m) for the 6 x M4 screws. (2 x M4 screws recommended for mounting the package on the heatsink and the 4 screws given with the screw version).
- The screws supplied with the package are adapted for mounting on a board (or others types of terminals) with a thickness of 0.6 mm min and 2.2 mm max.

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